

TOSHIBA Diode Silicon Epitaxial Planar Type

1SS302

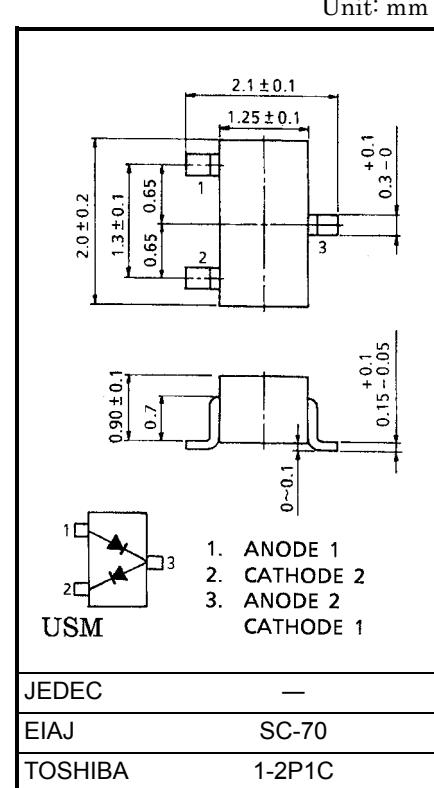
Ultra High Speed Switching Applications

- Small package : SC-70
- Low forward voltage : VF (3) = 0.90V (typ.)
- Fast reverse recovery time: trr = 1.6ns (typ.)
- Small total capacitance : CT = 0.9pF (typ.)

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V _{RM}	85	V
Reverse voltage	V _R	80	V
Maximum (peak) forward current	I _{FM}	300 (*)	mA
Average forward current	I _O	100 (*)	mA
Surge current (10ms)	I _{FSM}	2 (*)	A
Power dissipation	P	100	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~125	°C

*: Unit rating. Total rating = unit rating × 0.7

**Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F (1)	—	I _F = 1mA	—	0.60	—	V
	V _F (2)	—	I _F = 10mA	—	0.72	—	
	V _F (3)	—	I _F = 100mA	—	0.90	1.20	
Reverse current	I _R (1)	—	V _R = 30V	—	—	0.1	μA
	I _R (2)	—	V _R = 80V	—	—	0.5	
Total capacitance	C _T	—	V _R = 0, f = 1MHz	—	0.9	3.0	pF
Reverse recovery time	t _{rr}	—	I _F = 10mA, Fig.1	—	1.6	4.0	ns